

## 1N914 /DL914 FAST SWITCHING DIODE

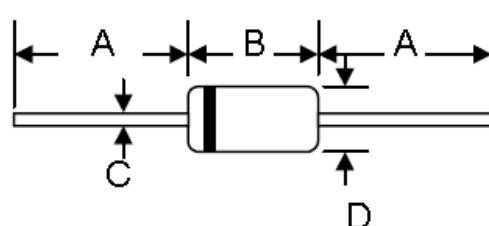
### Features:

- Fast Switching Speed
- Glass Package Version for High Reliability
- High Conductance
- Available in Both Through-Hole and Surface Mount Versions
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

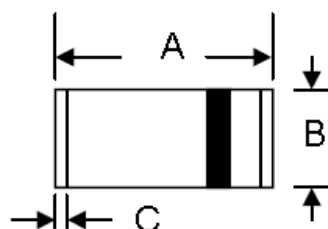
### Mechanical Data:

- Case: DO-35, DL-35
- Terminals: Plated leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: DO-35 0.13 grams  
DL-35 0.05 grams
- Marking: Part Name, SSG and Marking code for date code

### Mechanical Dimensions: In mm/Inches



1N914



DL914

DO-35				
Dim	Min	Max	Min	Max
A	25.40	—	1.000	—
B	—	4.00	—	0.157
C	—	0.60	—	0.024
D	—	2.00	—	0.079
	in mm		In inch	

MiniMELF				
Dim	Min	Max	Min	Max
A	3.30	3.70	0.130	0.146
B	1.30	1.60	0.051	0.063
C	0.28	0.50	0.011	0.020
	In mm		In inch	

**Maximum Ratings** @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Non- Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	75	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	53	V
Forward Current	I <sub>F</sub>	300	mA
Rectified Current(Average), Half Wave Rectification with Resistive Load and f≥50MHz (Note 1)	I <sub>O</sub>	150	mA
Non-Repetitive Peak Forward Surge Current @t=1.0s @t=1.0μs	I <sub>FSM</sub>	1.0 2.0	A
Power Dissipation Derate Above 25°C	P <sub>D</sub>	500 1.68	mW mW/°C
Typical Thermal Resistance, Junction to Ambient Air	R <sub>θJA</sub>	300	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +175	°C

**Electrical Characteristics** @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V <sub>FM</sub>	-	1.0	V	@I <sub>F</sub> =10mA
Reverse Leakage Current	I <sub>RM</sub>	-	5.0 50 30 25	uA uA uA nA	@V <sub>R</sub> =75V @V <sub>R</sub> =70V, T <sub>J</sub> =150°C @V <sub>R</sub> =20V, T <sub>J</sub> =150°C @V <sub>R</sub> =20V
Capacitance	C <sub>T</sub>	-	4	pF	V <sub>R</sub> =0V, f=1.0MHz
Reverse Recovery Time	t <sub>rr</sub>	-	4	ns	I <sub>F</sub> =10mA to I <sub>R</sub> =1.0mA, V <sub>R</sub> =6V, R <sub>L</sub> =100Ω

Note: 1. Diode on Substrate substrate 10×8×0.7mm

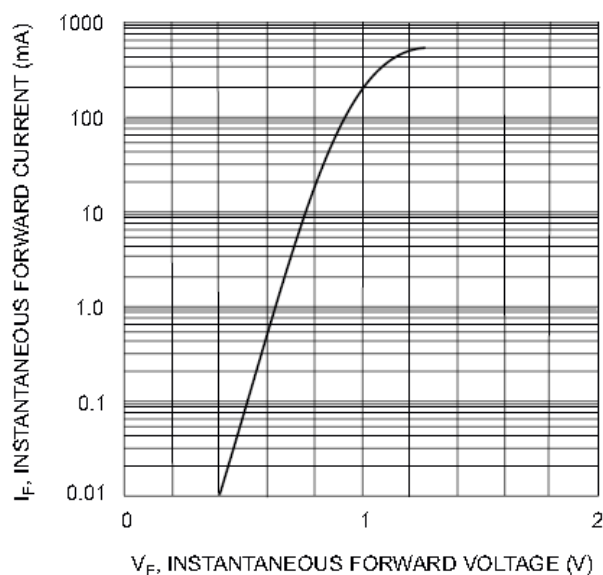


Fig. 1 Forward Characteristics

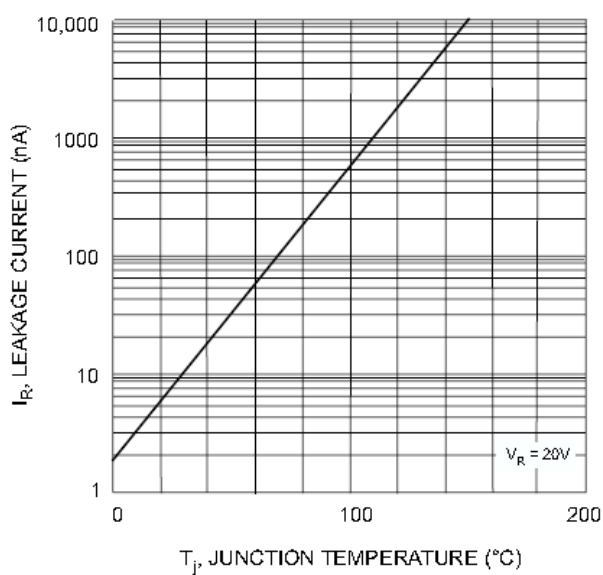


Fig. 2 Leakage Current vs Junction Temperature

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